Zibo Seno Electronic Engineering Co., Ltd.

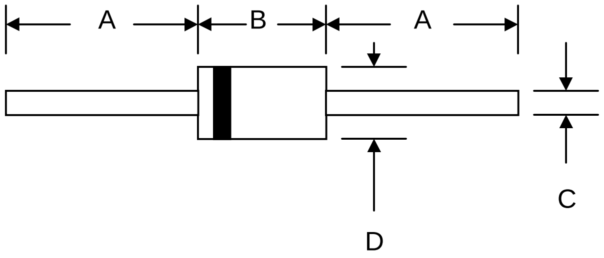
淄博圣诺

HER501 – HER508

5.0A ULTRAFAST DIODE

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability



DO-201AD		
Dim	**Min**	**Max**
A	24.5	—
B	7.20	9.50
C	1.10	1.30
D	5.00	5.60
All Dimensions in mm		

Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free: For RoHS / Lead Free Version**

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	HER 501	HER 502	HER 503	HER 504	HER 505	HER 506	HER 507	HER 508	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	420	560	700	V
Average Rectified Output Current (Note 1) @T_A = 55°C	I_O	5.0								A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	150								A
Forward Voltage @I_F = 5.0A	V_{FM}	1.0				1.3	1.7			V
Peak Reverse Current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	10 100								µA
Reverse Recovery Time (Note 2)	t_{rr}	50					75			nS
Typical Junction Capacitance (Note 3)	C_j	80					50			pF
Operating Temperature Range	T_j	-65 to +150								°C
Storage Temperature Range	T_{STG}	-65 to +150								°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case
2. Measured with IF = 0.5A, IR = 1.0A, IRR = 0.25A. See figure 5.
3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

HER501 – HER508

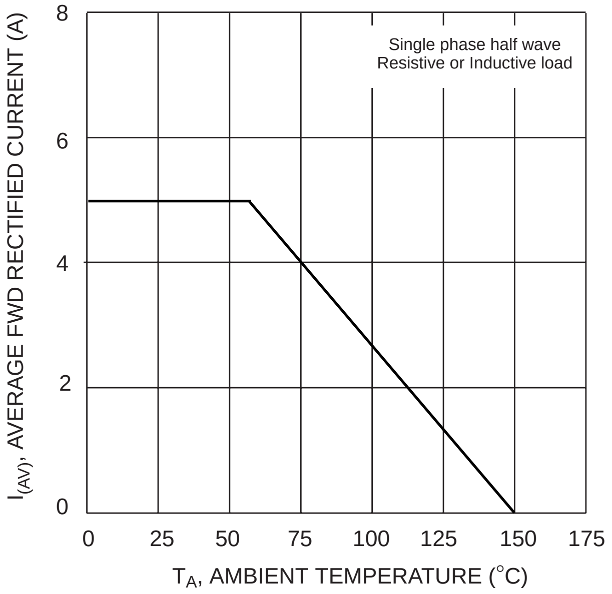


Fig. 1 Forward Current Derating Curve

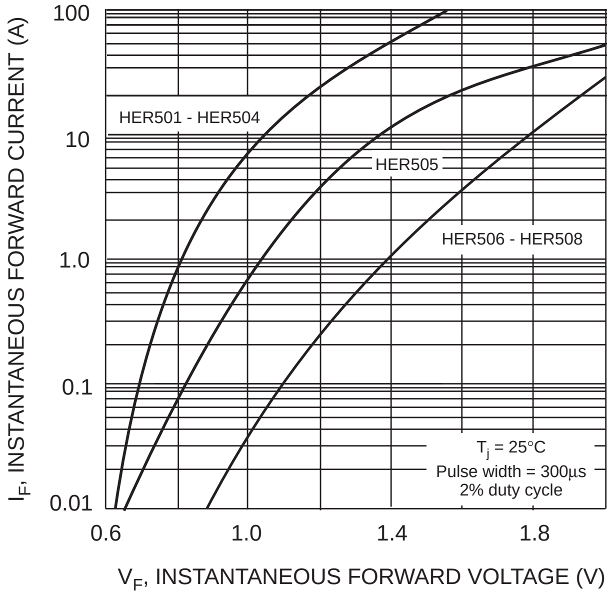


Fig. 2 Typical Forward Characteristics

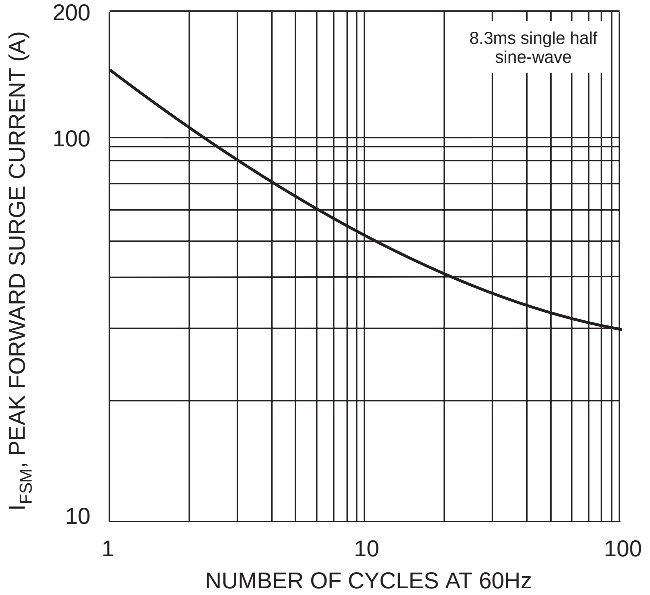


Fig. 3 Peak Forward Surge Current

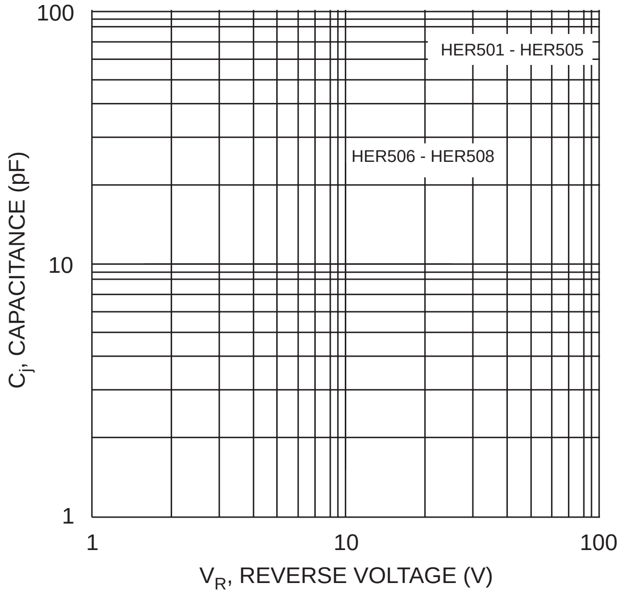
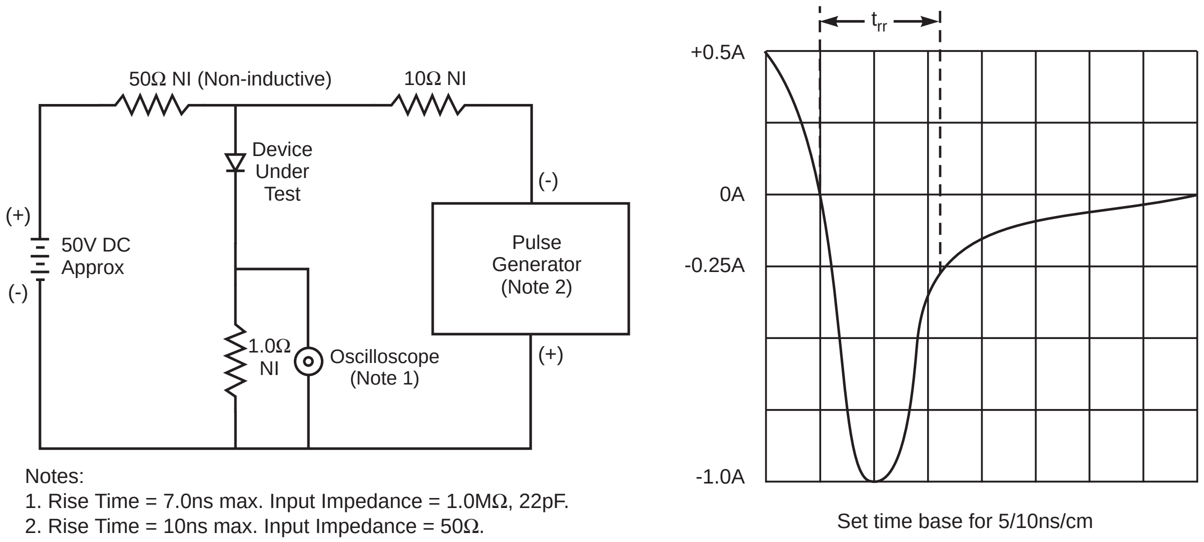


Fig. 4 Typical Junction Capacitance



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
2. Rise Time = 10ns max. Input Impedance = 50Ω.

Set time base for 5/10ns/cm

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit